QA tests of the CBM Silicon Tracking System sensors with an infrared laser

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March 14, 2016





Introduction

Silicon Tracker System design:

- Detector acceptance
 - rapidities from centre-of-mass to beampipe
 - angular coverage $2.5^{\circ} < \Theta < 25.0^{\circ}$
- Low mass large area detector
 - readout electronics away from the acceptance
 - double sided 300 μm thick silicon sensors (8 stations)
 - material budget $\simeq 1\% X_0/\text{station}$
 - low scattering, high momentum resolution
 - track matching in MVD and RICH/MUCH
- To fulfil requirements above well understanding of our sensors is needed
- See A. Lymanets, Mo HK15 talk for more details

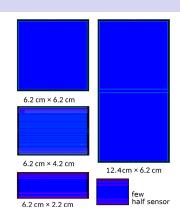


- $\Delta p/p \simeq 1.5\%$
- up to $\simeq 25\,\mu\mathrm{m}$ single hit resolution

Microstrip sensor prototypes

- Double-sided n-type silicon sensors
 - ▶ $58 \, \mu \text{m}$ pitch
 - ▶ 1024 strips per sensor
 - ► AC-coupling, aluminium strips
 - 7.5° stereo angle for p-side (suppression of the ghost track rate)
- Sensor inside a sandwich PCB frame:

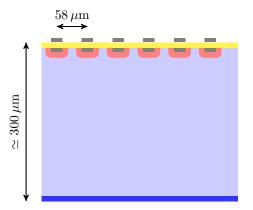




- radiation tolerance up to $10^{14}\,\mathrm{n_{eg}/cm^2}$
- signal transfer to r/o electronics by microcable (polyimide $10~\mu\mathrm{m}$, aluminium $14~\mu\mathrm{m}$ thick)

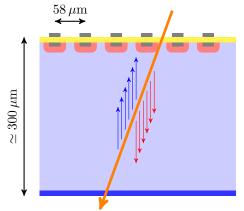
interaction with MIP

- MIP (Minimum Ionising Particle) penetrates silicon sensor
- Deposited charge drifts along \vec{E} field to the electrodes

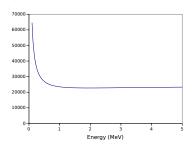


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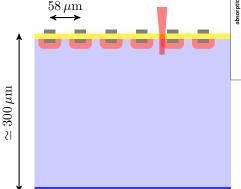


- $\Delta E = 3.79 \pm 0.01 \, \mathrm{eV}$ per one e-h pair got from
 - C. Bussolati et al. Phys. Rev. 136, A1756]
- ullet Δ_p is found for 300 $\mu\mathrm{m}$ silicon
- $\Delta_p \simeq 23 \times 10^3$
- this value depends on many input parameters



interaction with (infra)red laser

- (Infra)red laser can be used to mimic MIPs
- Deposited charge drifts along \vec{E} field to the electrodes





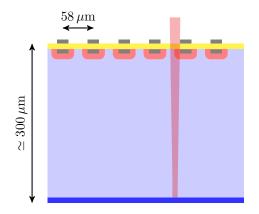
Silicon absorption depth

[Green MA, Keevers MJ. 1995;3:189 - 192.]:

- red light (660 nm)
 4 μm
- infrared light (1060 nm) $901 \mu m$

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Laser:

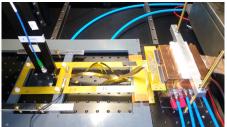
- ▶ infrared 1060 nm
- triggered by external puls generator

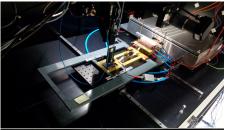
Focuser:

- focusing distance $10 \pm 1 \, \mathrm{mm}$
- beam size $12 \pm 2 \, \mu \mathrm{m}$
- Step motor
 - controlled by EPICS
 - positioning precision $\simeq 1\,\mu\mathrm{m}$
- Data acquisition
 - ► DABC over optical channel (ver. 2012)
 - ► GO4 online monitoring

Laser test stand

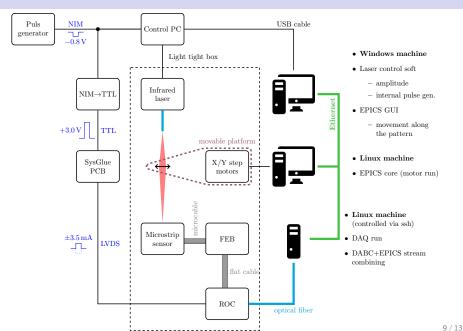
- Constructed for studies of the sensor properties with a laser
- Sensor + readout + laser in a light tight box
- Readout controllers additionally shielded





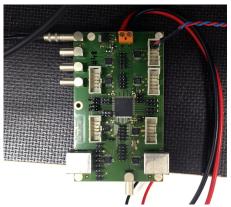


Laser test stand scheme



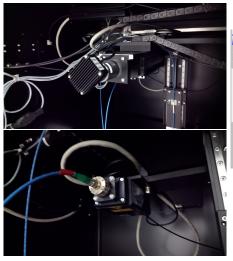
External triggering system



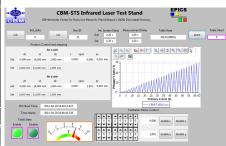


- **1** NIM signal is generated $(-0.8 \,\mathrm{V})$
- 2 signal to Laser control PC
- \odot converted to TTL signal $(+3\,\mathrm{V})$

Positioning system

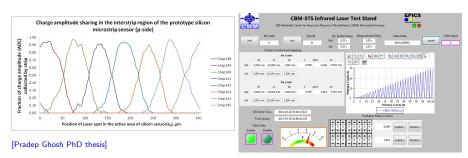


Vertiacal positioning is manual



- Automated X/Y positioning
- \bullet Accuracy up to $1\,\mu\mathrm{m}$
- Scanning along predefined pattern with EPICs based software

Online monitor and data processing



- Charge sharing between neighbouring strips
- Focusing is complicated with manual z-positioning
- External trigger forces to r/o all 128 channels per pulse

Conclusions and outlook

- Infrared laser is a good tool to test silicon sensor prototypes
- Red laser may be used for cross-check/surface effect studies
- Laser test stand is ready for operation
- Application of the external triggering allows go deep below the noise

Things we still missing:

- Motorised z-positioning for the focusing purposes
- Online feed-back from data stream for the pattern correction:
 - misalignment correction
 - automatic focusing
- Remote control for hardware components: bias voltage, pulse generator...
- Automatise the procedure for the QA during the mass production

